Analog Power AM20N10-250DE MOSFET Datasheet

http://www.manuallib.com/analog-power/am20n10-250de-mosfet-datasheet.html

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N-Channel 100-V (D-S) MOSFET

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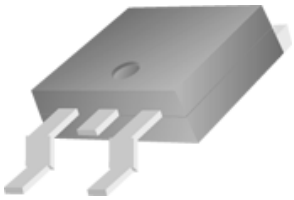
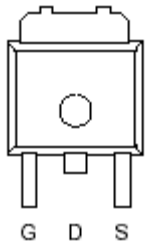
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
100	280 @ V_{GS} = 10V	11
	355 @ V_{GS} = 4.5V	10

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology

ESD Protected
2000V



TO-252



Top View

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[a]	T_C=25°C	I_D	11	A
Pulsed Drain Current[b]		I_{DM}	36	
Continuous Source Current (Diode Conduction)[a]		I_S	30	A
Power Dissipation[a]	T_C=25°C	P_D	50	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient[a]	$R_{\theta JA}$	50	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	3.0	°C/W

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	1.0			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V			±10	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V			1	μA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 55°C			25	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	34			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 4.5 A			280	mΩ
		V_{GS} = 4.5 V, I_D = 4 A			355	
Forward Tranconductance[A]	g_{fs}	V_{DS} = 15 V, I_D = 4.5 A		5		S
Diode Forward Voltage	V_{SD}	I_S = 9 A, V_{GS} = 0 V		1		V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 50 V, V_{GS} = 5.5 V, I_D = 4.5 A		10		nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			7.8		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 11.1 Ω , I_D = 4.5 A, V_{GEN} = 10 V		4.8		nS
Rise Time	t_r			4		
Turn-Off Delay Time	$t_{d(off)}$			12.8		
Fall-Time	t_f			4		

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

Package Information